Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

Panasonic

MOS FET FK6K06120L

Unit: mm

FK6K06120L Single N-channel MOS FET

For lithium-ion secondary battery protection circuits For load switching

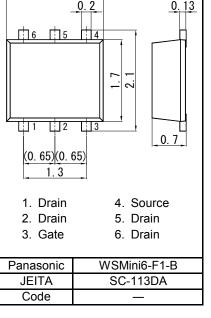
Features

- Low drain-source ON resistance: RDS(on) typ. = 60 m Ω (VGS = 4.5 V) ٠
- Low drive voltage: 2.5 V drive
- RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol: 5J

Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

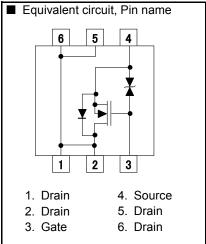
■ Absolute Maximum Ratings Ta = 25 °C								
Parameter		Symbol	Rating	Unit				
Drain-Source Voltage		VDS	60	V				
Gate-source Voltage		VGS	±20					
Drain Current	Ta = 25°C, t = 10sec *1	ID1	4.2					
	Ta = 25°C, DC ^{*1} Ta = 25°C, DC ^{*2} Ta = 25°C, DC ^{*3}	ID2	3.4 4.8 2.3	А				
	Pulsed, Tch < 150°C ^{*1}	IDp	12					
Total Power Dissipation	Ta = 25°C, DC ^{*1}	PD	0.9	W				
Thermal Resistance	Junction to Ambient	Rθja	145	°C / W				
Channel Temperature		Tch	150	°C				
Storage Temperature Range		Tstg	-55 to +150	U				



Package dimension

0.2

2.0



- Note *1 Mounted on FR-4 glass epoxy board, 25.4mm x 25.4mm x t 1.0mm coated with copper foil > 500 mm^2 .
 - *2 Mounted on Ceramic substrate, 70.0mm x 70.0mm x t 1.0mm
 - *3 Mounted on FR-4 glass epoxy board, 25.4mm x 25.4mm x t 1.0mm

Panasonic

MOS FET FK6K06120L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	60			V	
Zero Gate Voltage Source Current	IDSS	VDS = 60 V, VGS = 0 V			10	μA	
Gate-source Leakage Current	IGSS	VGS = ±20 V, VDS = 0 V			±10	μA	
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	0.6		2.0	V	
Drain-source On-state Resistance	RDS(on)1	ID = 1.5 A, VGS = 4.5 V	-	60	76	m0	
Drain-source on-state Resistance	RDS(on)2	ID = 1.5 A, VGS = 2.5 V	-	70	110	mΩ	
Input Capacitance ^{*1}	Ciss			400			
Output Capacitance ^{*1}	Coss	VDS = 30 V, VGS = 0 V, f = 1 MHz		30		pF	
Reverse Transfer Capacitance *1	Crss			20			
Turn-on delay Time *1,*2	td(on)	VDD = 30 V, VGS = 0 to 10 V		10		ne	
Rise Time ^{*1,*2}	tr	ID = 1.5 A		15		ns	
Turn-off delay Time *1,*2	td(off)	VDD = 30 V, VGS = 10 to 0 V		45		ne	
Fall Time *1,*2	tf	ID = 1.5 A		40		ns	
Total Gate Charge ^{*1}	Qg	VDD = 30 V		10			
Gate-source Charge *1	Qgs	VGS = 0 to 10 V		1.0		nC	
Gate-drain Charge ^{*1}	Qgd	ID = 3 A		1.5			
Body Diode Forward Voltage	VSD	IF = 1.5 A, VGS = 0 V		0.8	1.2	V	

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

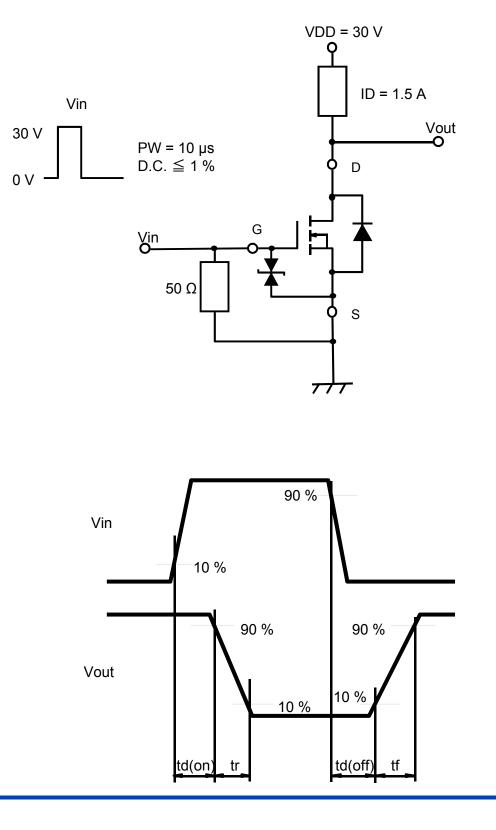
*1 Assured by design

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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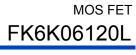


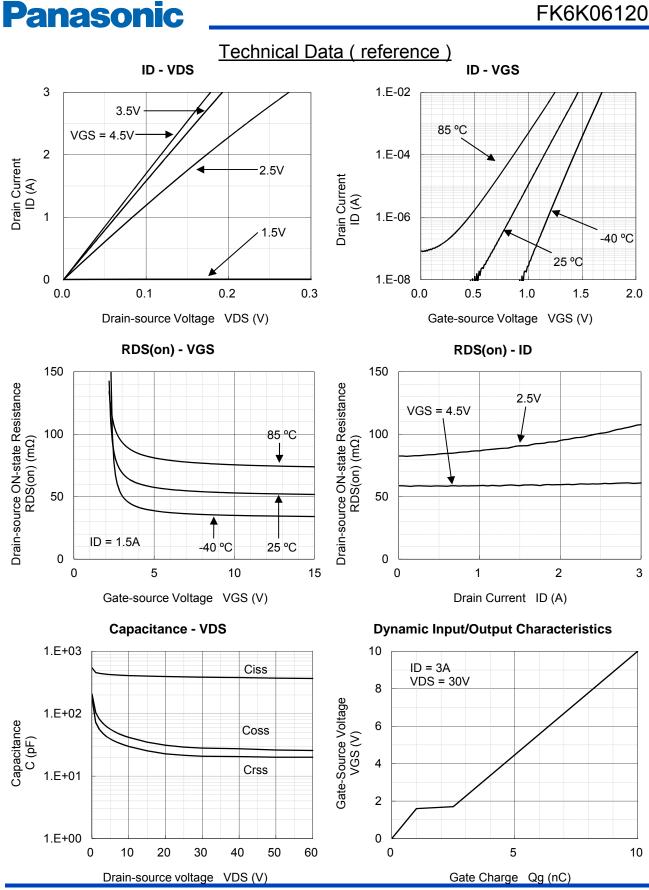
*2 Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

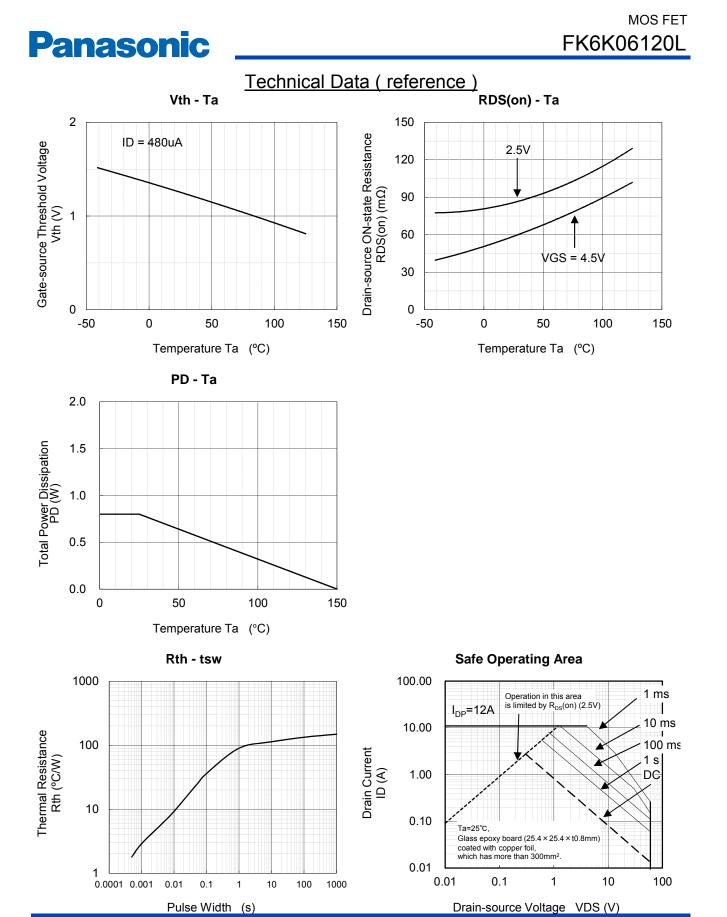


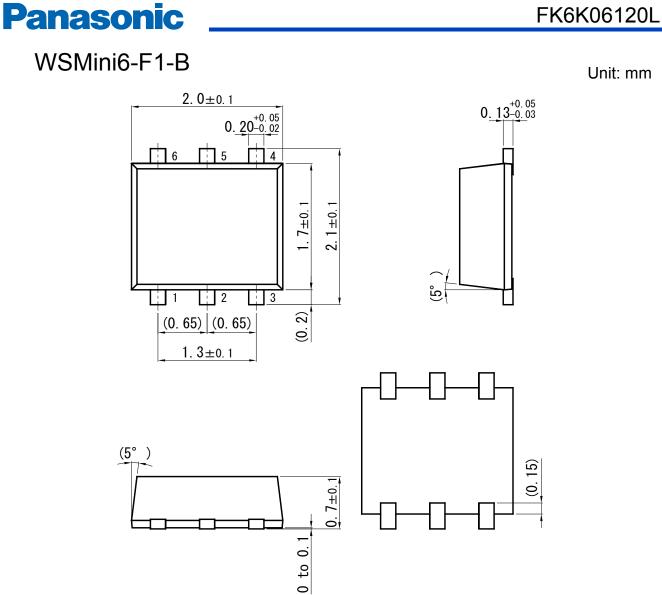
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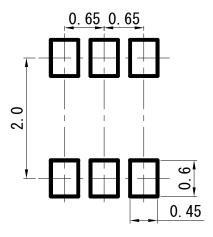








Land Pattern (Reference) (Unit : mm)



Unit: mm

MOS FET

Established : 2014-08-18 Revised : 2015-03-02

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